PRELIMINARY

SOLID STATE DEVICES, INC

14849 Firestone Boulevard · La Mirada,CA 90638
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424

SFF250/61

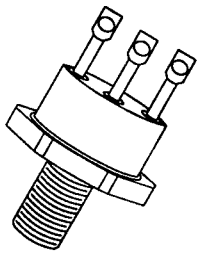
30 AMP
200 VOLTS
0.085 Ω
N-CHANNEL
POWER MOSFET

Designer's Data Sheet

FEATURES:

- Rugged construction with poly silicon gate
- Low RDS(on) and high transconductance
- Excellent high temperature stability
- Very fast switching speed
- Fast recovery and superior dv/dt performance
- Increased reverse energy capability
- Low input and transfer capacitance for easy paralleling
- Hermetically sealed power package
- TX, TXV and Space Level screening available
- Replaces: IRF250 Types

TO-61



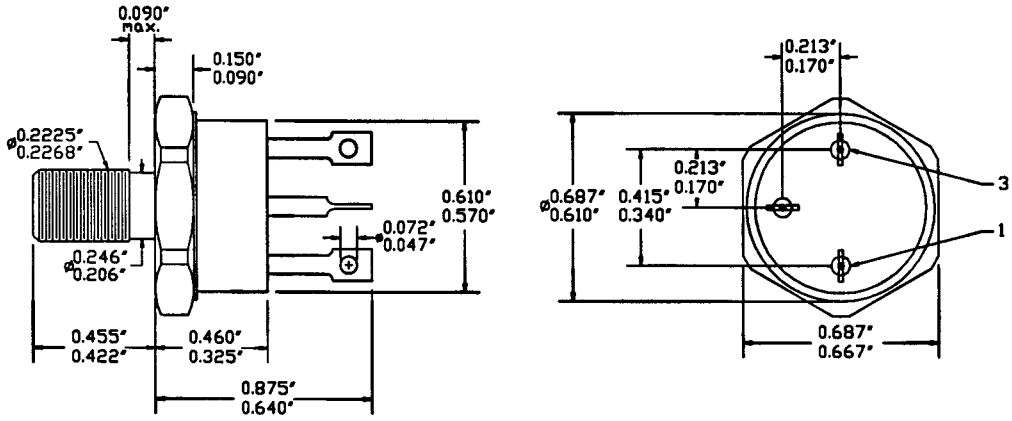
MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	VALUE	UNIT
Drain to Source Voltage	V_{DS}	200	Volts
Gate to Source Voltage	V_{GS}	± 20	Volts
Continuous Drain Current	I_D	30	Amps
Operating and Storage Temperature	T_{op} & T_{stg}	-55 to +150	°C
Thermal Resistance, Junction to Case	$R_{\theta JC}$	4	°C/W
Total Device Dissipation @ TC=25°C Total Device Dissipation @ TC=55°C	P_D	125 95	Watts

PACKAGE OUTLINE: TO-61

PIN OUT:

PIN 1: SOURCE
PIN 2: GATE
PIN 3: DRAIN



NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.	DATA SHEET #: F00055 B	MED

SFF250/61

PRELIMINARY

SOLID STATE DEVICES, INC

14849 Firestone Boulevard · La Mirada,CA 90638
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424

ELECTRICAL CHARACTERISTICS @ TJ=25°C (Unless Otherwise Specified)

RATING		SYMBOL	MIN	TYP	MAX	UNIT
Drain to Source Breakdown Voltage (VGS=0 V, ID=250µA)		BVDSS	200	---	---	V
Drain to Source on State Resistance (VGS=10 V, ID=60% Rated ID		RDS(on)	---	0.08	0.085	Ω
On State Drain Current (VDS >ID(on) X RDS(on) Max, VGS=10 V		ID(on)	30	---	---	A
Gate Threshold Voltage (VDS=VGS, ID=250µA)		VGS(th)	2	3	4	V
Forward Transconductance (VDS >ID(on) X RDS(on) Max, IDS=60% rated ID)		gfs	13	15	---	S(℧)
Zero Gate Voltage Drain Current (VDS=80% rated voltage, VGS=0 V) (VDS=80% rated VDS, VGS=0 V, TA=125°C)		IDSS	--- ---	--- ---	250 1000	µA
Gate to Source Leakage Forward **Gate to Source Leakage Reverse**	At rated VGS	IGSS	--- ---	--- ---	100 -100	nA
Total Gate Charge **Gate to Source Charge** **Gate to Drain Charge**	VGS=10 Volts 50% rated VDS Rated ID	Qg Qgs Qgd	--- --- ---	80 12 44	120 20 65	nC
Turn on Delay Time **Rise Time** **Turn Off Delay Time** **Fall Time**	VDD=50% rated VDS 50% rated ID RG= 6.2 Ω	td(on) tr td(off) tf	--- --- --- ---	20 120 70 80	30 180 100 120	nsec
Diode Forward Voltage (IS=rated ID, VGS=0 V, TJ=25°C)		VSD	---	1.1	2.0	V
Diode Reverse Recovery Time **Reverse Recovery Charge**	TJ=25°C IF=10A di/dt=100 A/µsec	trr QRR	140 1.8	300 3.8	630 8	nsec µC
Input Capacitance **Output Capacitance** **Reverse Transfer Capacitance**	VGS=0 Volts VDS=25 Volts f= 1 MHz	Ciss Coss Crss	--- --- ---	2600 650 150	--- --- ---	pF

